

Description

The AOD480-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.

TO-252-2L (DPAK)

General Features

 $V_{DS} = 30V I_{D} = 20A$

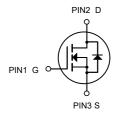
 $R_{DS(ON)}$ < 25m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AOD480-HXY	TO-252-2L(DPAK)	20N03 XXX YYYY	2500

Absolute Maximum Ratings (T_c=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
In@Tc=25°C	Continuous Drain Current, V _{GS} @ 10V ¹	20	Α
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	15	Α
Id@Ta=25°C	Continuous Drain Current, V _{GS} @ 10V ¹	7.3	Α
Id@Ta=70°C	Continuous Drain Current, V _{GS} @ 10V ¹	5.8	Α
Ідм	Pulsed Drain Current ²	50	Α
EAS	Single Pulse Avalanche Energy ³	8.1	mJ
las	Avalanche Current	12.7	Α
P _D @T _C =25°C	Total Power Dissipation ⁴	20.8	W
P _D @T _A =25°C	Total Power Dissipation ⁴	2	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R _θ JA	Thermal Resistance Junction-ambient ¹	62	°C/W
Rejc	Thermal Resistance Junction-Case ¹	6	°C/W



Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
$\triangle BV$ DSS/ $\triangle T$ J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA		0.023		V/°C	
		V _{GS} =10V , I _D =10A		18	25		
Rds(on)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =8A		25	38	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage		1.0	1.2	2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250uA		-4.2		mV/°C	
lana	Drain-Source Leakage Current	V_{DS} =24V , V_{GS} =0V , T_{J} =25 $^{\circ}$ C			1	uA	
IDSS		V _{DS} =24V , V _{GS} =0V , T _J =55°C			5		
Igss	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =10A		5.5		S	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.3		Ω	
Qg	Total Gate Charge (4.5V)			4.9			
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =10A		1.66		nC	
Qgd	Gate-Drain Charge			1.85			
Td(on)	Turn-On Delay Time			1.6			
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		15.8			
Td(off)	Turn-Off Delay Time	R _G =3.3		13		ns	
Tf	Fall Time	I _D =10A		4.8			
Ciss	Input Capacitance			416			
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		62		pF	
Crss	Reverse Transfer Capacitance			51			
Is	Continuous Source Current ^{1,5}				24	Α	
Іѕм	Pulsed Source Current ^{2,5}	−V _G =V _D =0V , Force Current			50	Α	
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V	
trr	Reverse Recovery Time	I _F =10A , dI/dt=100A/μs ,		8.7		nS	
Qrr	Reverse Recovery Charge			1.95		nC	

Note:

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2The data tested by pulsed, pulse width. The EAS data shows Max. rating.

3he test condition is V $\! \leq \! 300 us$, duty cycle $_{DD=25} \! \leq \! V,\! V$ 2% $_{GS}$ =10V,L=0.1mH,I $_{AS}$ =12.7A

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

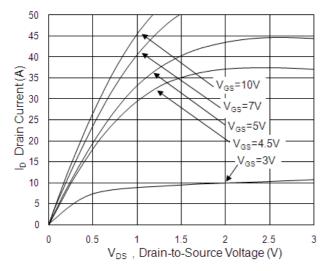


Fig.1 Typical Output Characteristics

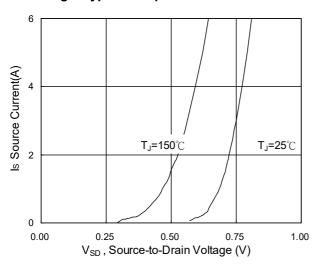


Fig.3 Forward Characteristics Of Reverse

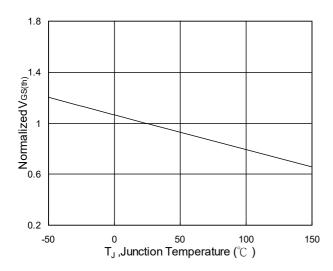


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_J

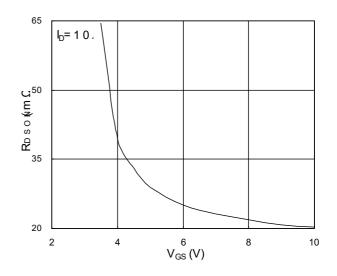


Fig.2 On-Resistance vs. Gate-Source

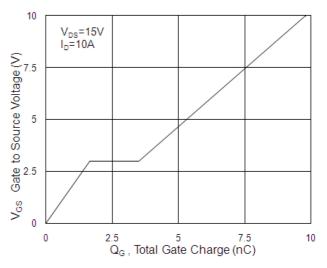


Fig.4 Gate-Charge Characteristics

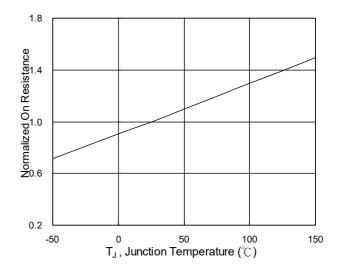
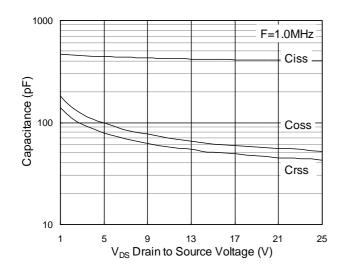


Fig.6 Normalized R_{DSON} vs. T_J





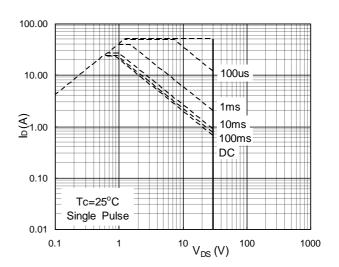


Fig.7 Capacitance

Fig.8 Safe Operating Area

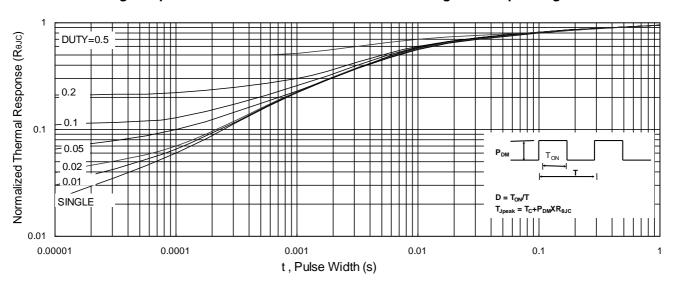


Fig.9 Normalized Maximum Transient Thermal Impedance

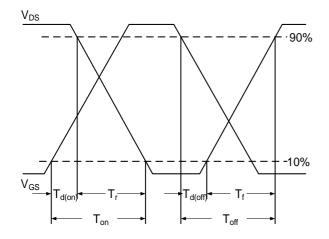


Fig.10 Switching Time Waveform

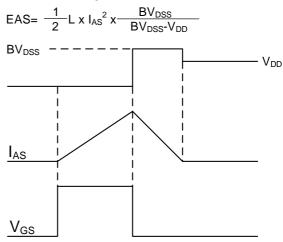
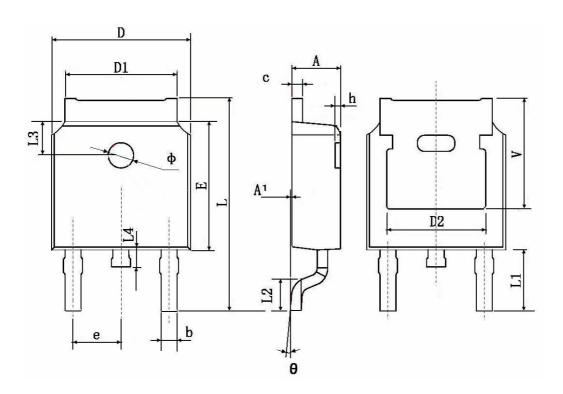


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



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